

BUK7608-55A

N-channel TrenchMOS standard level FET Rev. 03 — 14 June 2010

Product data sheet

Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	55	V
l _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	[1]	-	-	75	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2		-	-	254	W
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 175 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 11}}{\text{Figure 12}};$		-	-	16	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{see } \frac{\text{Figure 12}}{\text{Figure 12}};$		-	6.8	8	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_D = 75 \text{ A}$; $V_{sup} \le 55 \text{ V}$; $R_{GS} = 50 \Omega$; $V_{GS} = 10 \text{ V}$; $T_{j(init)} = 25 \text{ °C}$; unclamped	-	-	670	mJ
Dynamic cl	haracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 0 \text{ V; } I_D = 25 \text{ A;}$ $V_{DS} = 44 \text{ V; } T_j = 25 \text{ °C;}$ see Figure 13	-	35	-	nC

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain ^[1]	mb	D D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7608-55A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	55	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	55	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u>	-	-	126	Α
		T _{mb} = 100 °C; V _{GS} = 10 V; see <u>Figure 1</u>	[2]	-	-	75	Α
		T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	[2]	-	-	75	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \mu s$; pulsed; see Figure 3		-	-	504	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	254	W
T _{stg}	storage temperature			-55	-	175	°C
Tj	junction temperature			-55	-	175	°C
Source-drain	n diode						
Is	source current	T _{mb} = 25 °C	[2]	-	-	75	Α
			[1]	-	-	126	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	504	Α
Avalanche ru	uggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 75 A; $V_{sup} \le$ 55 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	670	mJ

^[1] Current is limited by power dissipation chip rating.

^[2] Continuous current is limited by package.

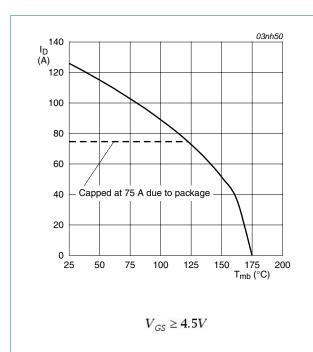
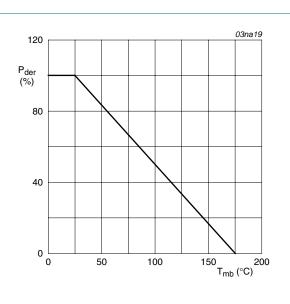
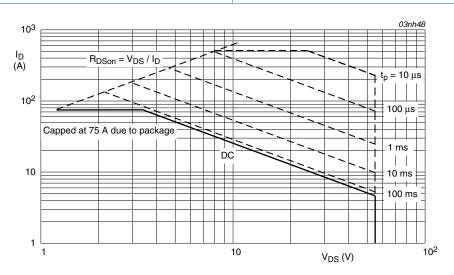


Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



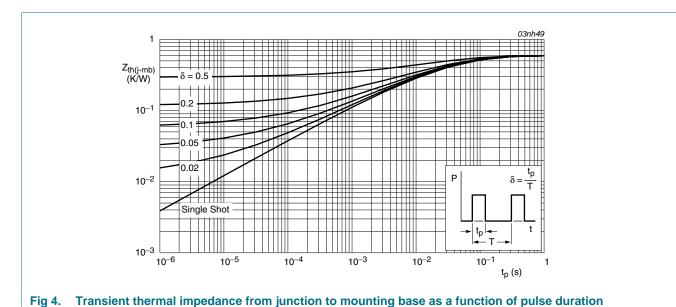
 $T_{mb} = 25$ °C; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.59	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on printed-circuit board; minimum footprint	-	50	-	K/W



6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
()	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 10	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	4.4	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		V _{DS} = 55 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	10	μΑ
I _{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}$; $I_D = 25 \text{ A}$; $T_j = 175 \text{ °C}$; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	16	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	6.8	8	mΩ
Dynamic (characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 0 \text{ V};$	-	76	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 13</u>	-	16	-	nC
Q_{GD}	gate-drain charge		-	35	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	3264	4352	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	719	863	pF
C _{rss}	reverse transfer capacitance		-	390	533	pF
d(on)	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	24	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 \text{ °C}$	-	94	-	ns
d(off)	turn-off delay time		-	100	-	ns
t _f	fall time		-	80	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die ; $T_j = 25$ °C	-	2.5	-	nΗ
		from drain lead 6 mm from package to centre of die; $T_j = 25$ °C	-	4.5	-	nΗ
-s	internal source inductance	from source lead to source bond pad ; $T_j = 25~^{\circ}\text{C}$	-	7.5	-	nΗ
Source-dr	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 15</u>	-	0.85	1.2	V
·rr	reverse recovery time	$I_S = 75 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$;	-	65	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	170	-	nC

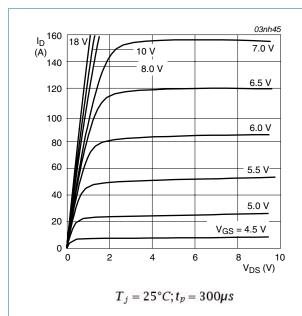


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

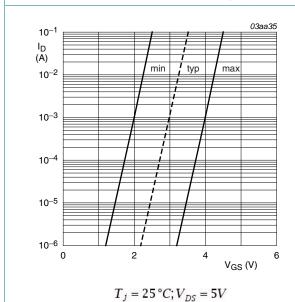
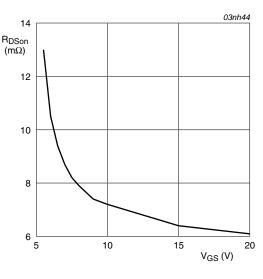


Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25^{\circ}C; I_D = 25A$

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

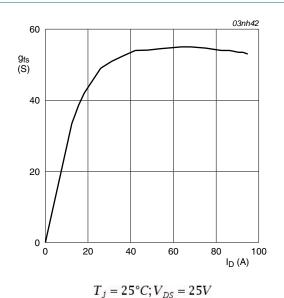


Fig 8. Forward transconductance as a function of drain current; typical values

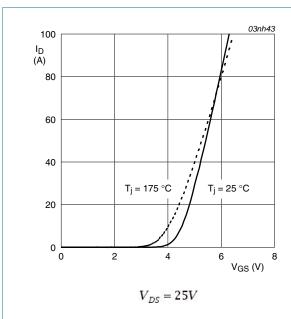


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

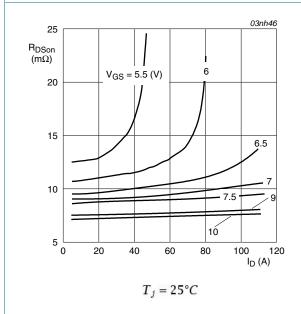
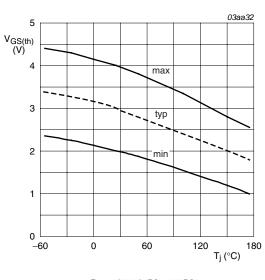


Fig 11. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 1 mA; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

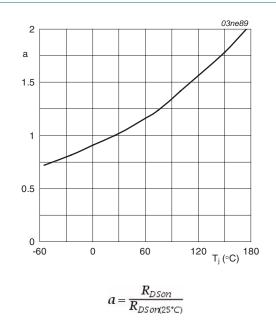


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

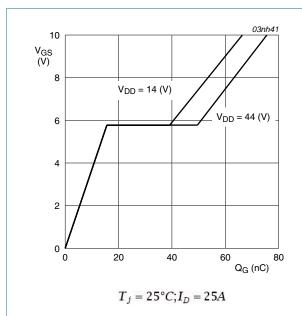
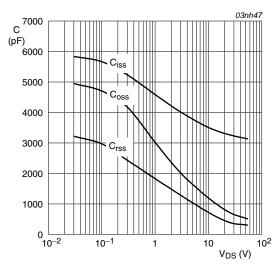


Fig 13. Gate-source voltage as a function of turn-on gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

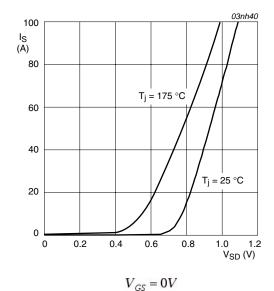


Fig 15. Reverse diode current as a function of reverse diode voltage; typical values

7. Package outline

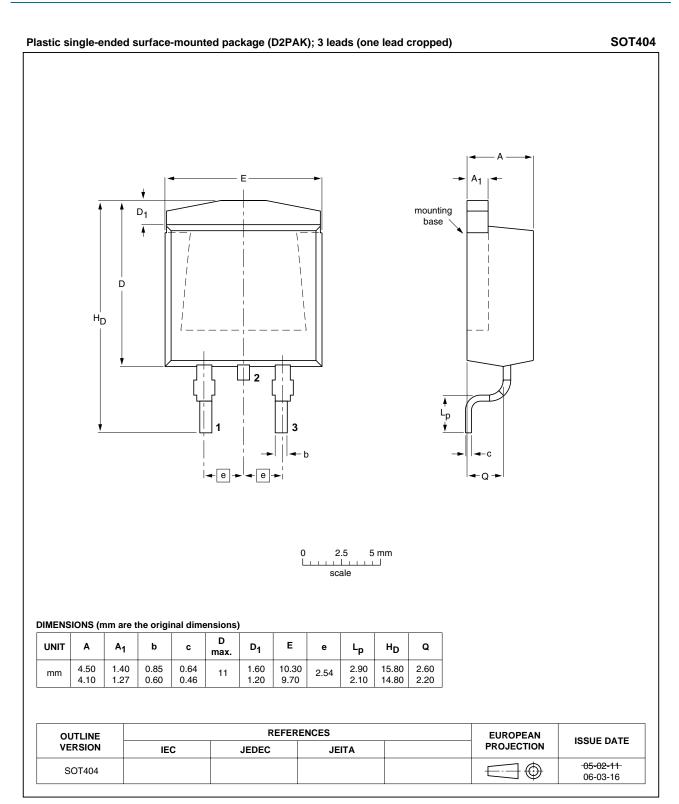


Fig 16. Package outline SOT404 (D2PAK)

Revision history

Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7608-55A v.3	20100614	Product data sheet	-	BUK7508_7608_55A v.2
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guideli of NXP Semiconductors. 			
	 Legal texts I 	have been adapted to the	new company name where	appropriate.
	 Type number 	er BUK7608-55A separate	d from data sheet BUK7508	3_7608_55A v.2.
BUK7508_7608_55A v.2	20020117	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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N-channel TrenchMOS standard level FET

11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values3
5	Thermal characteristics5
6	Characteristics6
7	Package outline10
8	Revision history11
9	Legal information12
9.1	Data sheet status
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks13
10	Contact information13

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